

FOD817 Series

DESCRIPTION

The FOD817 Series consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 4-pin dual in-line package.

FEATURES

- · Applicable to Pb-free IR reflow soldering
- Compact 4-pin package
- · Current transfer ratio in selected groups:

FOD817: 50-600% FOD817A: 80-160% FOD817B: 130-260% FOD817C: 200-400% FOD817D: 300-600%

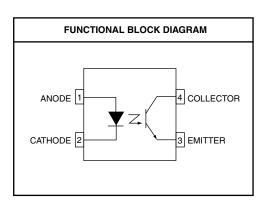
- C-UL, UL and VDE approved
- · High input-output isolation voltage of 5000 Vrms

APPLICATIONS

FOD817 Series

- Power supply regulators
- · Digital logic inputs
- Microprocessor inputs





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C Unless otherwise specified.)				
Parameter	Symbol	Value	Units	
TOTAL DEVICE				
Storage Temperature	T _{STG}	-55 to +125	°C	
Operating Temperature	T _{OPR}	-30 to +100	°C	
Lead Solder Temperature	T _{SOL}	260 for 10 sec	°C	
Total Device Power Dissipation	P _D	200	mW	
EMITTER				
Continuous Forward Current	I _F	50	mA	
Reverse Voltage	V _R	6	V	
LED Power Dissipation	P _D	70	mW	
Derate above 25°C	LD LD	0.93	mW/°C	
DETECTOR				
Collector-Emitter Voltage	V _{CEO}	70	V	
Emitter-Collector Voltage	V _{ECO}	6	V	
Continuous Collector Current	I _C	50	mA	
Detector Power Dissipation	P _D	150	mW	
Derate above 25°C	L L D	2.0	mW/°C	



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ELECTRICAL CHARACTERISTICS (T _A = 25°C Unless otherwise specified.)						
INDIVIDUAL COMPONENT CHARACTERISTICS						
Parameter	Test Conditions	Symbol	Min	Тур*	Max	Unit
EMITTER Input Forward Voltage	(I _F = 20 mA)	V _F	_	1.2	1.4	٧
Reverse Leakage Current	$(V_R = 4.0 \text{ V})$	I _R	_	_	10	μΑ
Terminal Capacitance	(V = 0, f = 1 kHz)	C _t	_	30	250	pF
DETECTOR						
Collector-Emitter Breakdown Voltage	$(I_C = 0.1 \text{ mA}, I_F = 0)$	BV_CEO	70	-	—	V
Emitter-Collector Breakdown Voltage	$(I_E = 10 \mu A, I_F = 0)$	BV _{ECO}	6	_	_	V
Collector-Emitter Dark Current	$(V_{CF} = 20 \text{ V}, I_F = 0)$	I _{CEO}	_	_	100	nA

^{*}Typical values at $T_A = 25$ °C.

TRANSFER CHARACTERISTICS (T _A = 25°C Unless otherwise specified.)							
DC Characteristic	Test Conditions	Symbol	Device	Min	Тур*	Max	Unit
			FOD817	50	_	600	%
			FOD817A	80	_	160	%
Current Transfer Ratio	$(I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}) \text{ (note 1)}$	CTR	FOD817B	130	_	260	%
			FOD817C	200	_	400	%
			FOD817D	300	_	600	%
Collector-Emitter Saturation Voltage	(I _F = 20 mA, I _C = 1 mA)	V _{CE (SAT)}		_	0.1	0.2	٧
AC Characteristic							
Rise Time	$(I_C = 2 \text{ mA}, V_{CE} = 2 \text{ V}, R_L = 100\Omega) \text{ (note 2)}$	t _r		_	4	18	μs
Fall Time	$(I_C = 2 \text{ mA}, V_{CE} = 2 \text{ V}, R_L = 100\Omega) \text{ (note 2)}$	t _f		_	3	18	μs

ISOLATION CHARACTERISTICS						
Characteristic	Test Conditions	Symbol	Min	Тур*	Max	Units
Input-Output Isolation Voltage (note 3)	f = 60Hz, t = 1 min	V _{ISO}	5000			Vac(rms)
Isolation Resistance	(V _{I-O} = 500 VDC)	R _{ISO}	5 x 10 ¹⁰	10 ¹¹		Ω
Isolation Capacitance	$(V_{I-O} = 0, f = 1 \text{ MHz})$	C _{ISO}		0.6	1.0	pf

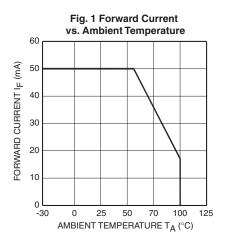
^{*}Typical values at $T_A = 25$ °C.

NOTES

- 1. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
- 2. For test circuit setup and waveforms, refer to page 4.
- 3. For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.

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Typical Electrical/Optical Characteristic Curves (T_A = 25°C Unless otherwise specified.)



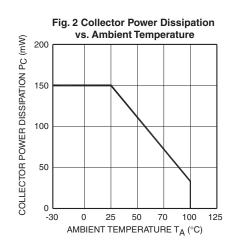


Fig. 3 Collector-Emitted Saturation Voltage vs. Forward Current

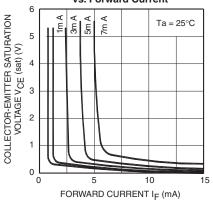


Fig. 4 Forward Current vs. Forward Voltage

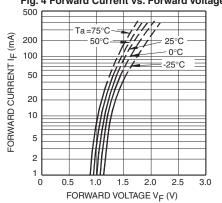


Fig. 5 Current Transfer Ratio vs. Forward Current

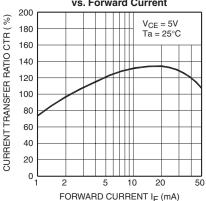
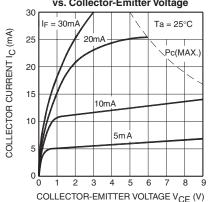


Fig. 6 Collector Current vs. Collector-Emitter Voltage



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Fig. 7. Relative Current Transfer Ratio

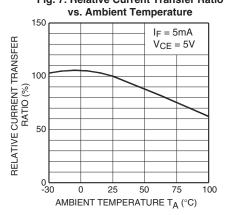


Fig. 8 Collector-Emitter Saturation Voltage

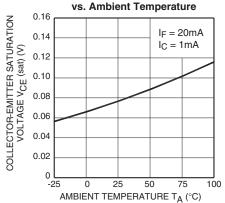


Fig. 9 Collector Dark Current vs. Ambient Temperature

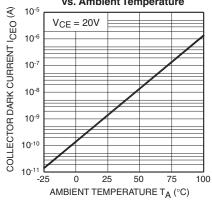


Fig. 10. Response Time

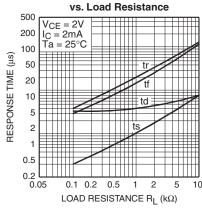
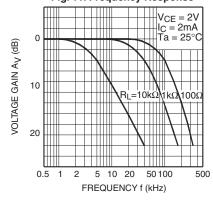
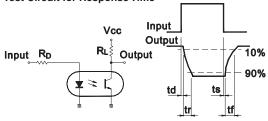


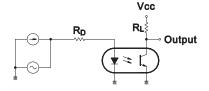
Fig. 11. Frequency Response



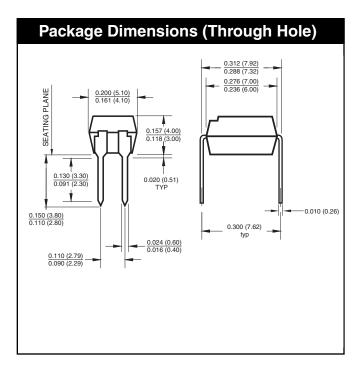
Test Circuit for Response Time

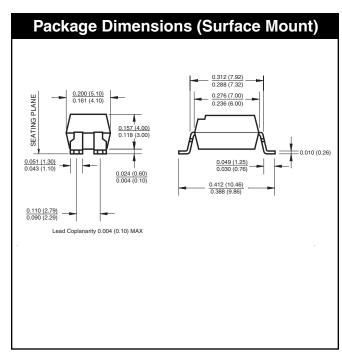


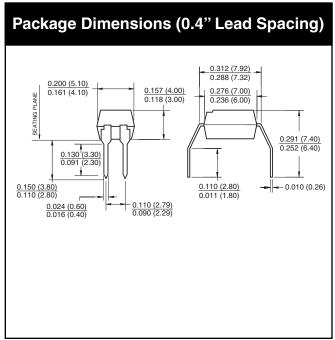
Test Circuit for Frequency Response

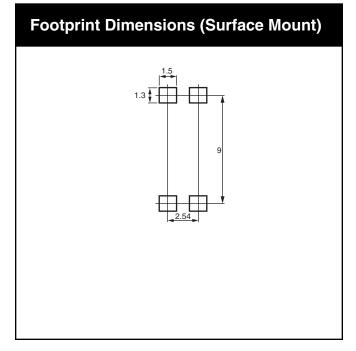


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NOTEAll dimensions are in inches (millimeters)

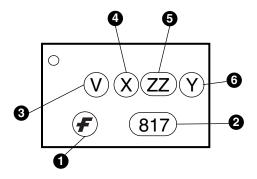


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ORDERING INFORMATION

Option	Order Entry Identifier	Description	
S	.S	Surface Mount Lead Bend	
SD	.SD	Surface Mount; Tape and reel	
W	.W	0.4" Lead Spacing	
300	.300	VDE 0884	
300W	.300W	VDE 0884, 0.4" Lead Spacing	
3S	.3S	VDE 0884, Surface Mount	
3SD	.3SD	VDE 0884, Surface Mount, Tape & Reel	

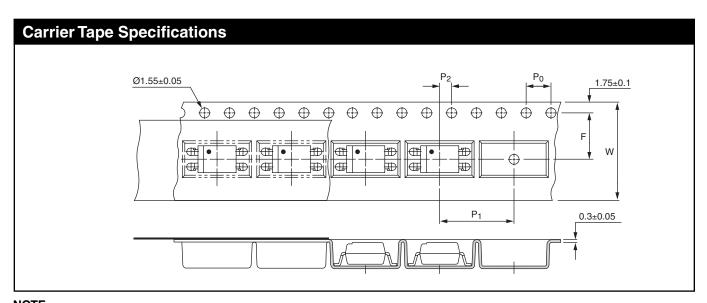
MARKING INFORMATION



Definitions			
1	Fairchild logo		
2	Device number		
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)		
4	One digit year code		
5	Two digit work week ranging from '01' to '53'		
6	Assembly package code		



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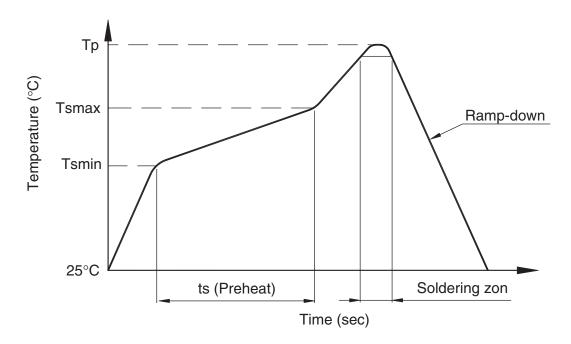


NOTEAll dimensions are in millimeters

Description	Symbol	Dimensions in mm (inches)
Tape wide	W	16 ± 0.3 (.63)
Pitch of sprocket holes	P ₀	4 ± 0.1 (.15)
Distance of compartment	F P ₂	7.5 ± 0.1 (.295) 2 ± 0.1 (.079)
Distance of compartment to compartment	P ₁	12 ± 0.1 (.472)

FOD817 Series

Lead Free recommended IR Reflow condition



Profile Feature	Pb-Sn solder assembly	Lead Free assembly
Preheat condition (Tsmin-Tsmax / ts)	100°C ~ 150°C 60 ~ 120 sec	150°C ~ 200°C 60 ~120 sec
Melt soldering zone	183°C 60 ~ 120 sec	217°C 30 ~ 90 sec
Peak temperature (Tp)	240 +0/-5°C	250 +0/-5°C
Ramp-down rate	6°C/sec max.	6°C/sec max.

Recommended Wave Soldering condition

Profile Feature	For all solder assembly	
Peak temperature (Tp)	Max 260°C for 10 sec	



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